



**umicore**  
*materials for a better life*

# Ge Substrates for Photonics and PV

Ensuring Supply Security, Advancing Recycling  
and Enabling CMOS Integration

Ivan Zyulkov  
CS International  
April 16<sup>th</sup>, 2024

# 2023 Key figures

Revenues

**€ 3.9 bn**

Colleagues

**11 565**

Adj. EBITDA

**€ 972 mn**

Adj. EBITDA  
margin

**25.0%**

ROCE

**13.5%**

Net zero

Scope 1 & 2 GHG emissions

**2035**

- ✓ Resilient performance with > € 200 mn PGM price and inflation headwinds
- ✓ While significantly stepping up investments for future growth

**Revenue:**

All revenue elements less the value of the following purchased metals: Au, Ag, Pt, Pd, Rh, Co, Ni, Pb, Cu, Ge, Li and Mn



# Our Group structure - EOM



Umicore Battery Materials

Battery Metals Refining

Automotive Catalysts

Precious Metals Chemistry

Fuel Cell & Stationary Catalysts

Precious Metals Management

Precious Metals Refining

Jewelry & Industrial Metals

Battery Recycling Solutions

**Electro-Optics Materials**

Metal Deposition Solutions

Cobalt & Specialty Materials

# Electro-Optic Materials

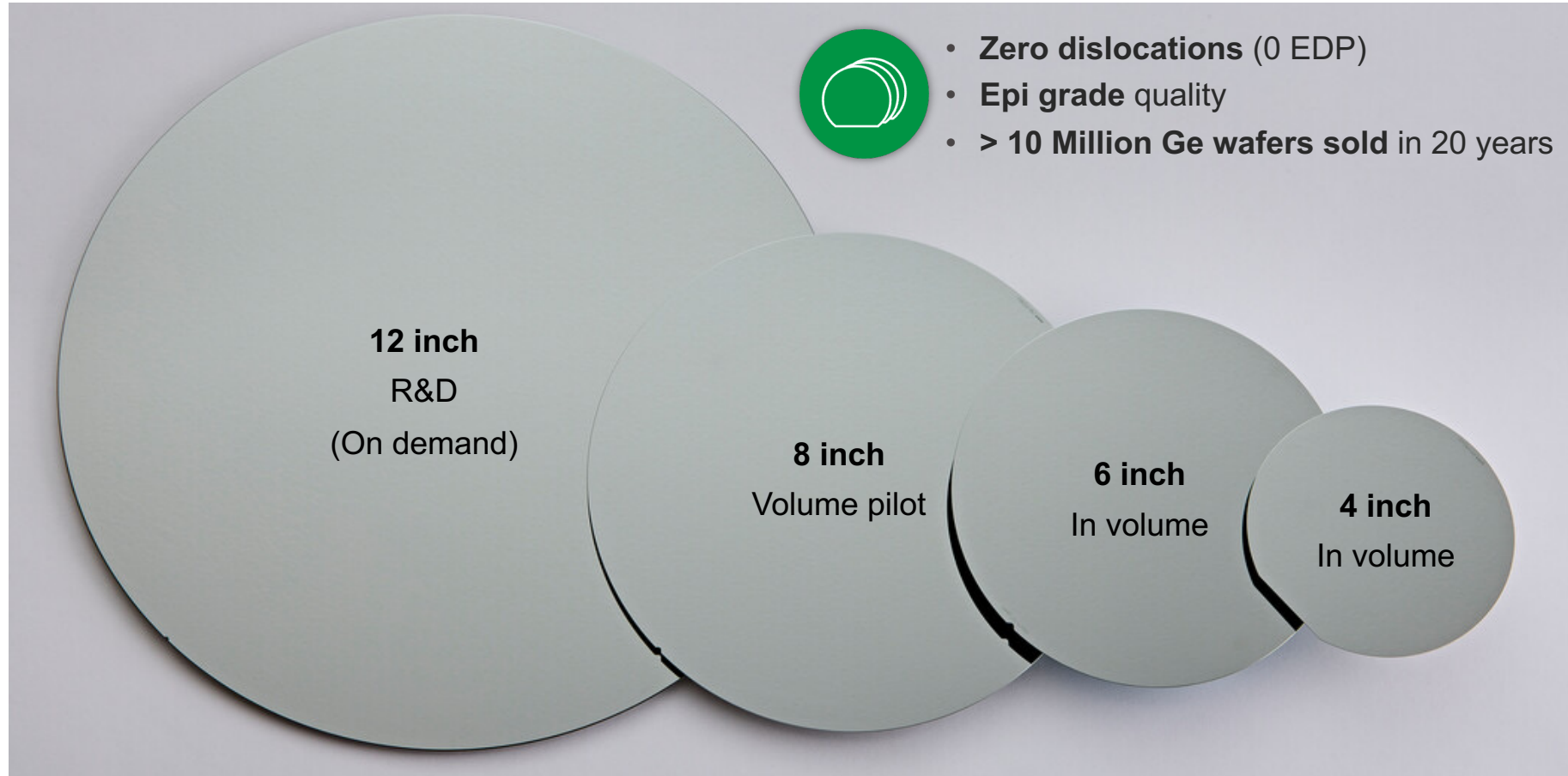
## 2 Business Lines



# Contents

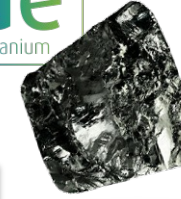
- Germanium properties and its applications.
- Photonics and PV applications of Ge substrates.
- Ge sourcing and Recycling.
- Reusable Ge platform.
- Conclusions.

# Umicore Germanium substrates



Umicore offers epi-ready Ge substrates of various diameters (from 4" to 12")

# Basic Germanium properties



Property	Silicon	GaAs	Germanium
Crystal structure	Diamond	Zincblende	Diamond
Density (g/cm <sup>3</sup> )	2.33	5.32	5.33
Lattice constant (Å)	5.430	5.653	5.658
Bandgap energy at 300K (eV)	1.12	1.42	0.66
Cut-off wavelength (μm)	1,06	0,87	1,6
Electron mobility (cm <sup>2</sup> /V-s)	1350	8500	3900
Hole mobility (cm <sup>2</sup> /V-s)	480	400	1900
Melting point (°C)	1415	1238	937
Thermal expansion (1/°C)	2.6 10 <sup>-6</sup>	5.7 10 <sup>-6</sup>	5.9 10 <sup>-6</sup>
Thermal conductivity (W/cm°C)	1.3	0.55	0.58
Fracture toughness (MPa.m <sup>1/2</sup> )	0.8	0.3	0.7
Young's modulus (GPa)	130-188	85-130	103-153

Si and Ge are elemental indirect semiconductors with similar up to 12" diameter 0 EPD\* crystal processes

Ge and GaAs are lattice matched

Ge cut-off wavelength enables SWIR photodiodes

Ge and GaAs have similar thermal expansion & conductivity

Ge is twice as tough as GaAs

Ge [100] is 18% less prompt to deformation vs GaAs

\* EPD: Etch pitch density, dislocation density



# PV applications

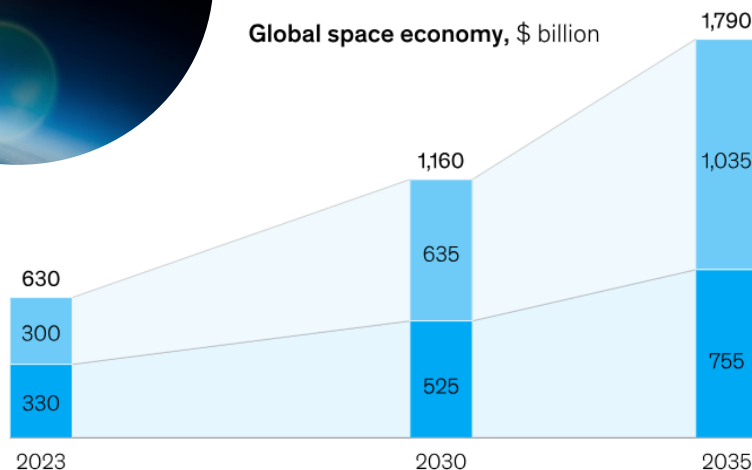
## MJ solar cells



### Space power

Space market is set to double by 2030, triple by 2035

Global space economy, \$ billion



Source: Future of Space Economy research



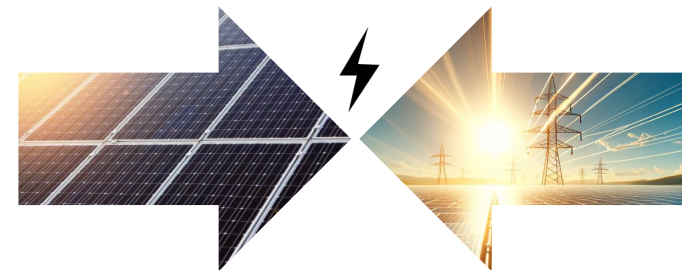
### Concentrated PV (CPV)

Re-birth of CPV - Expected to reach GW-scale as of 2030.



Space-grade high efficiency solar cells

Heat from the concentrated light

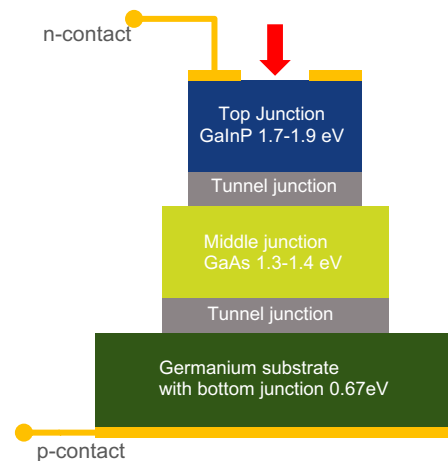


- Ge substrates are stronger than GaAs, thinner and more light weight, provide an extra solar cell junction.
- Swift growth in Space PV and CPV markets drives the demand for Ge substrates.

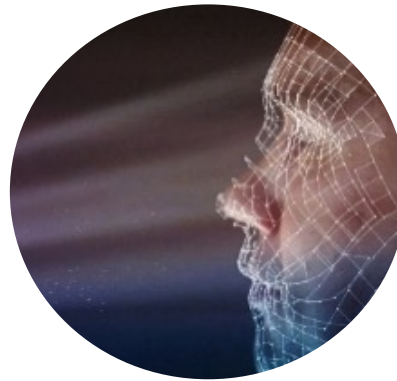


# Photonic applications

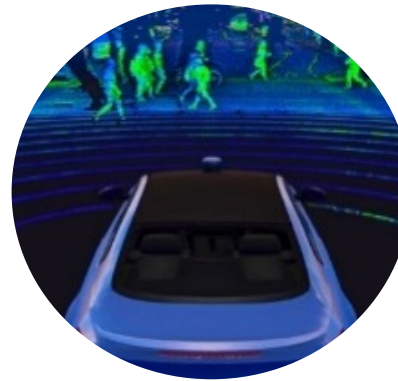
Ge lattice match with GaAs allows its use in various photonics application



Triple-junction solar cell structure



**VCSELs**  
3D sensing



**SWIR sensors**  
3D sensing



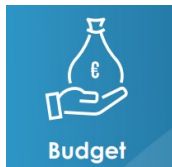
**Micro-LEDs**  
VR/MR

- Ge lattice constant is beneficial for several photonics applications.
- Multiple developments using Ge substrates in VCSELs, Sensors and micro-LEDs.

# Photogenic – Ge based VCSEL for automotive

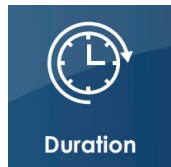


PHOTOGENIC

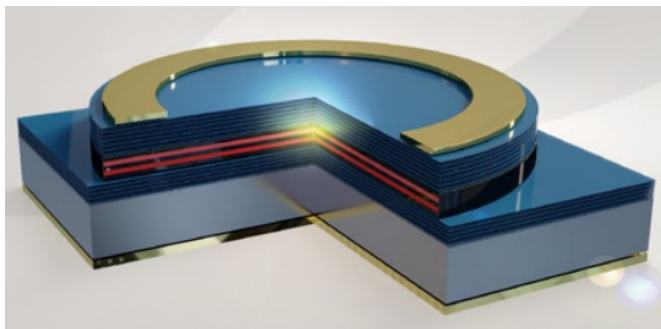


4.8 M euro

(100% EU-funded)



36 months



<https://horizon-photogenic.eu/>

TECHNIKON

TECHNIKON Forschungs- und  
Planungsgesellschaft mbH Austria  
(Villach)



Lodz University  
of Technology



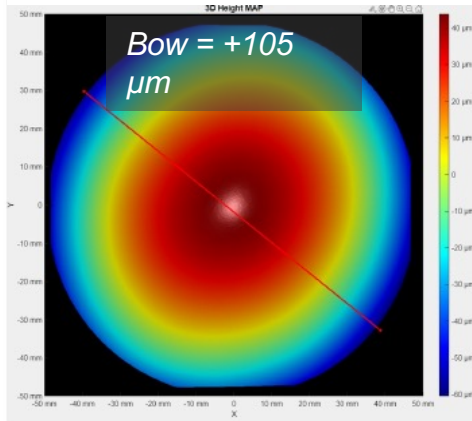
Funded by  
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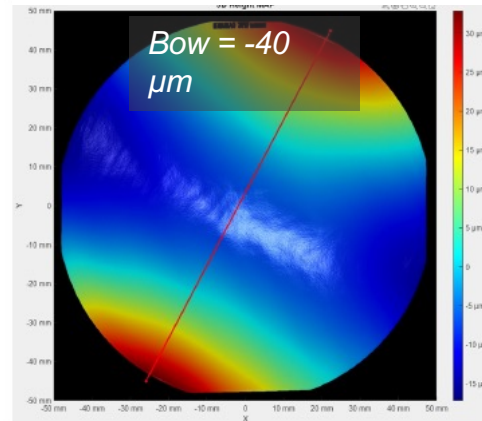
# Photogenic – Ge based VCSEL for automotive

- VIGO wafers measured by deflectometry at LAAS-CNRS
- GaAs/AlGaAs VCSELs are compressively stressed on GaAs but strain-balanced on Ge

VCSEL on 4" GaAs



VCSEL on 4" Ge



## Current status:

- Epitaxial growth on Ge with AlGaAs buffer layer
- Functional VCSELs on Ge substrate
- Ohmic contact on n-doped Ge
- Processing of first working devices

## Next steps:

- Further Improving Ge-VCSELs Epitaxy & Processing
- Design and Fabrication of Ge-VCSELs for LiDAR and iTOF systems

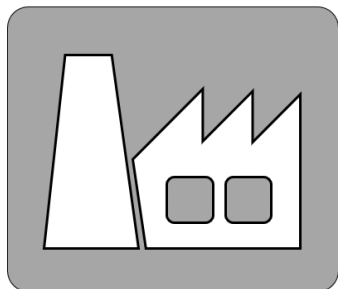


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# III-V processing in CMOS Fabs

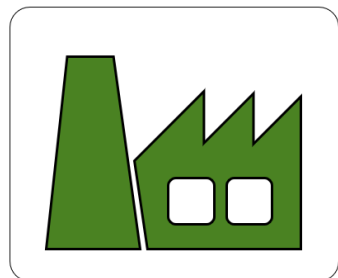
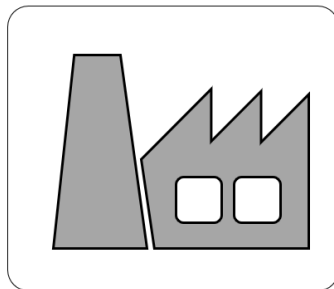
## III-V Foundry



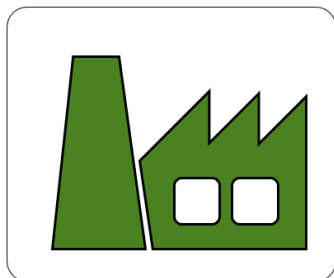
Small substrates  
Contamination (As)  
Si contamination



## CMOS Foundry



8-12" Ge substrates  
Ge wafers are  
CMOS compatible

CMOS offers a set of very advanced processing steps and low production cost in high volumes.

Ge substrate is compatible with CMOS production, while other III-V substrates are not (GaAs, InP, etc.)

Number of applications benefit from the integration between CMOS and III-V.

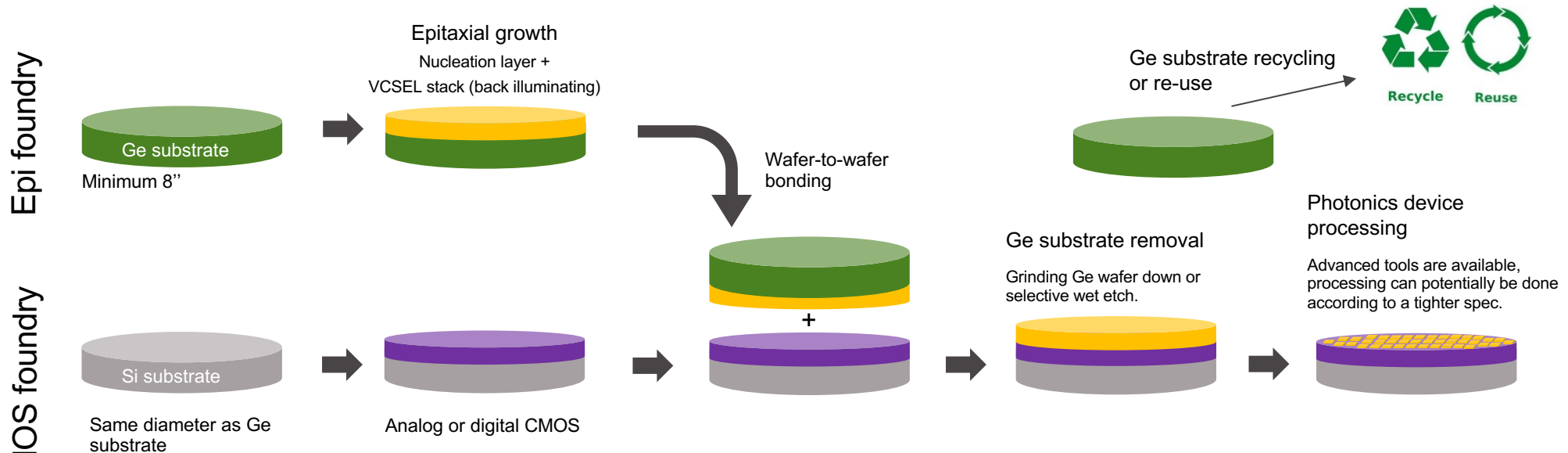
Ge substrate can be selectively removed and Ge metal can be recycled to recuperate a part of the substrate cost.

- Ge wafers allow III-V device manufacturing through CMOS fabs – new device concepts, high performance, low cost.
- Umicore 8" Ge wafers were tested at IMEC (e.g. lithography equipment).



# Potential avenue: CMOS & III-V fusion

Ge substrate can be selectively removed and recycled



- Ge wafers allow for III-V device processing performed at CMOS foundries.
- In addition, integration of Si CMOS with III-V is possible via wafer-to-wafer bonding.
- Wafer-to-wafer integration enables higher throughput = lower cost. Ge substrate removal avoids unnecessary waste generation and provides extra cost benefits.

# Growing Ge demand in all application segments

**MJ solar cells**  
Space PV

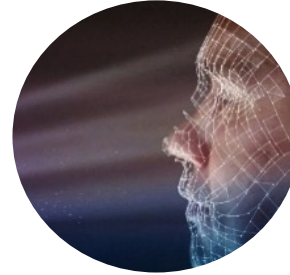


**MJ solar cells**  
CPV

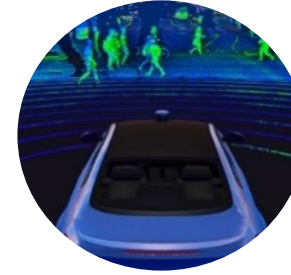


Rapid market growth for  
Ge-based solar cells

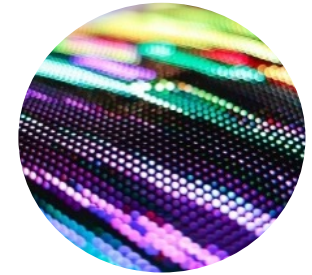
**VCSELs**  
3D sensing



**SWIR sensors**  
3D sensing



**Micro-LEDs**  
VR/MR



New device development, III-V integration with CMOS

# Breaking news from Jul 2023

Growing demand for Ge meets raw material supply constraints

GT Global Times

SOURCE / ECONOMY

## China to impose export controls on key materials for chipmaking as West's 'chip war' escalates

By Global Times

Published: Jul 03, 2023 09:36 PM



REUTERS

World Business Markets Sustainability Legal Breakingviews Technology Investig

### China exported no germanium, gallium in August after export curbs

By Amy Lv and Dominique Patton

September 20, 2023 12:56 PM GMT+2 - Updated 7 months ago



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Green is driving the US market

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- 'We have reached the limit.' Clash w
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## China hits back in the chip war, imposing export curbs on crucial raw materials

By Hanna Ziad and Xiaofei Xu, CNN

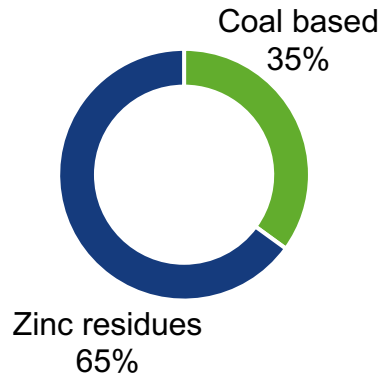
2 minute read · Published 12:27 PM EDT, Mon July 3, 2023



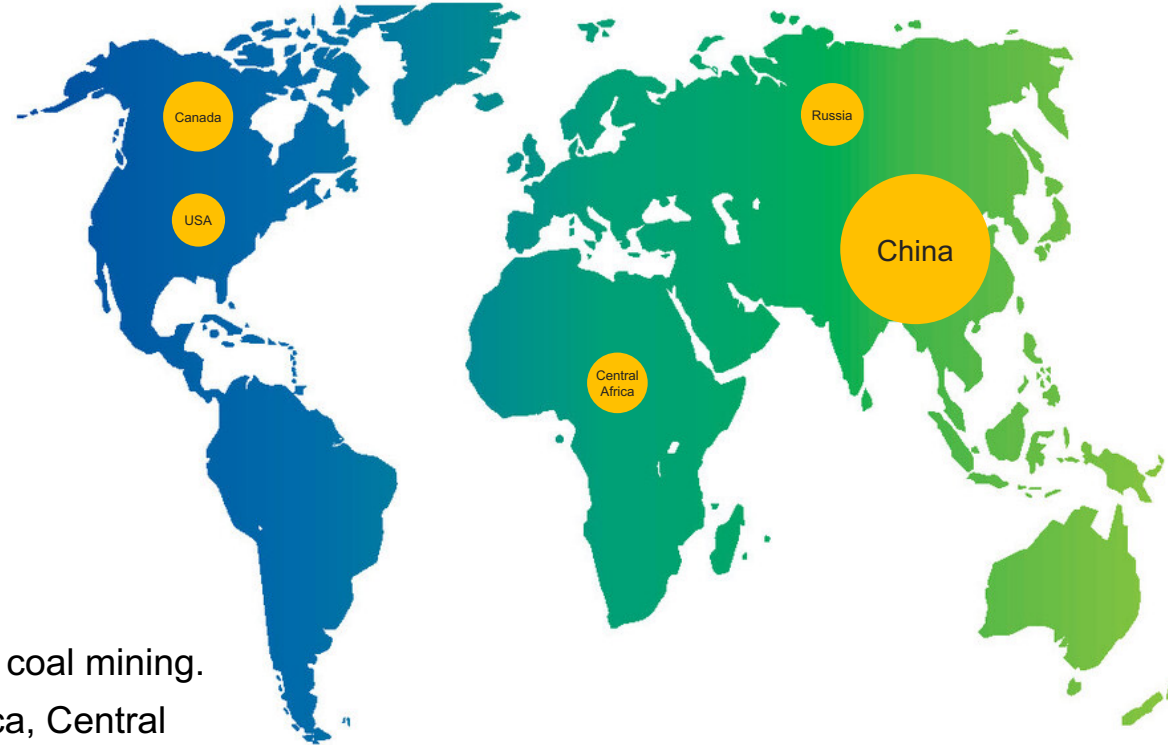
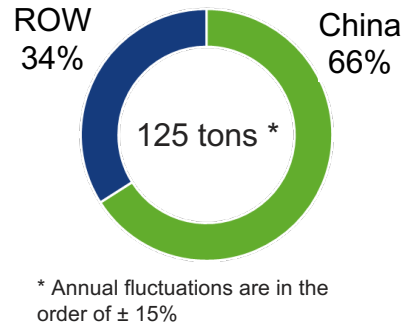
# Germanium primary sourcing

Relatively small market with a potential to grow its global supply

Type of global primary Ge supply



Origin of refined Ge worldwide



- Germanium is extracted out of feed from zinc and coal mining.
- Active sources are located in China, North-America, Central Africa and Russia.

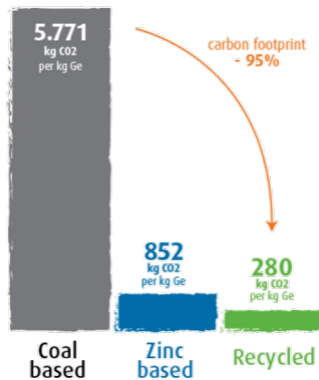


# Germanium – supply security through recycling

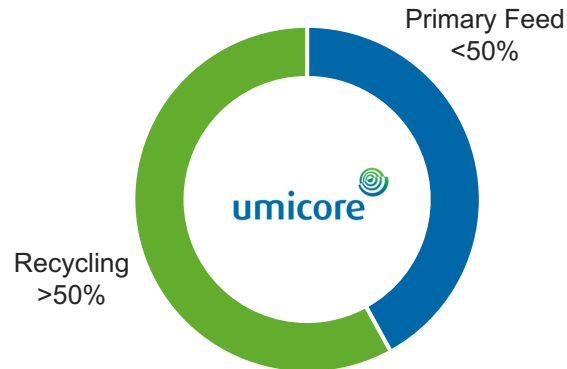
Umicore has well diversified Ge supply chain with above 50% coming from recycling



## Environmental impact of Ge sources



## Umicore Primary vs Secondary Sourcing (2022)

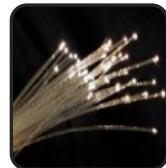


- No coal-based Ge in Umicore supply chain.
- Over 50% of our needs met through recycling; none from China.
- Recycling feed from all major Ge industries (fiber optics, solar, IR optics, LED, micro-electronics).
- Global supply diversification strategy active.
- Continual investment in innovations to reduce dependency upon primary sourcing



### Refining Sources

- Byproduct from Zinc mining



### Optical Fibers

- Scrubber solution/cake
- Soot & Preform glass
- Fiber waste



### Solar Cells & LED's

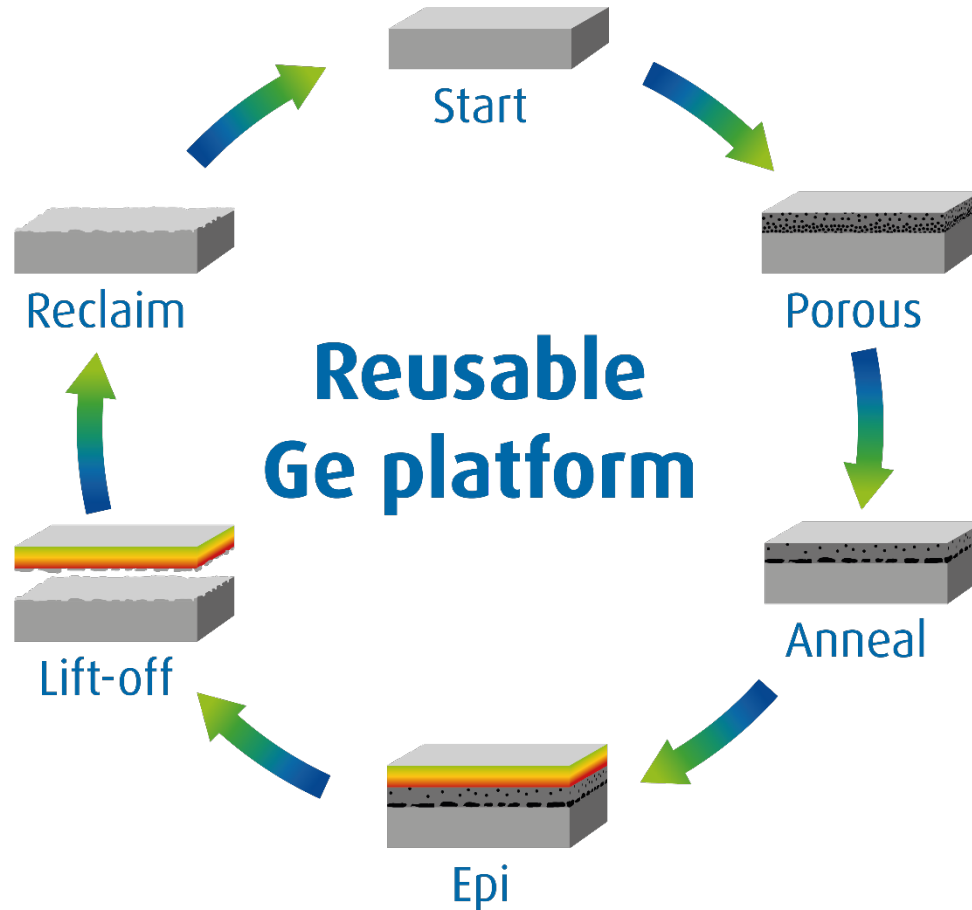
- Wafer scraps
- Grinding slurry
- Filter waste & Etch solution



### Infrared Optics

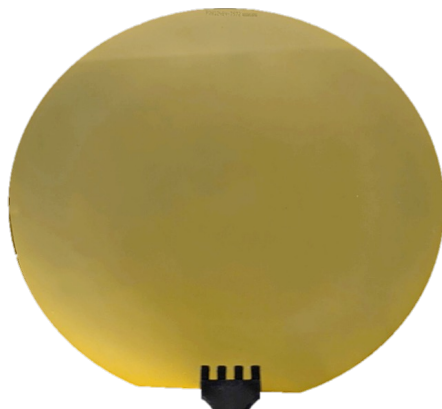
- Lens scraps
- Grinding/cutting slurry
- Sawing dust

## Next step in reducing primary sourcing dependency

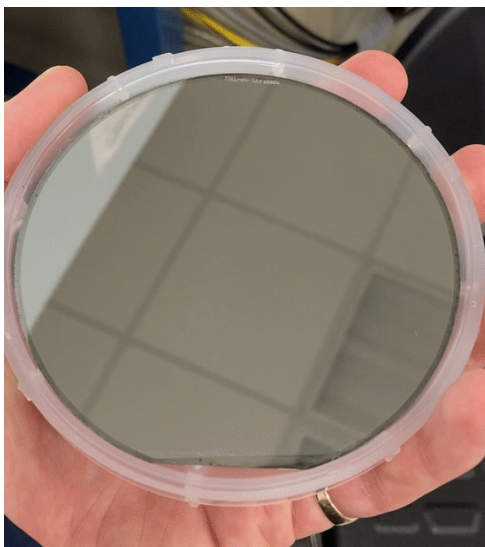


# Electrochemical porocification approach

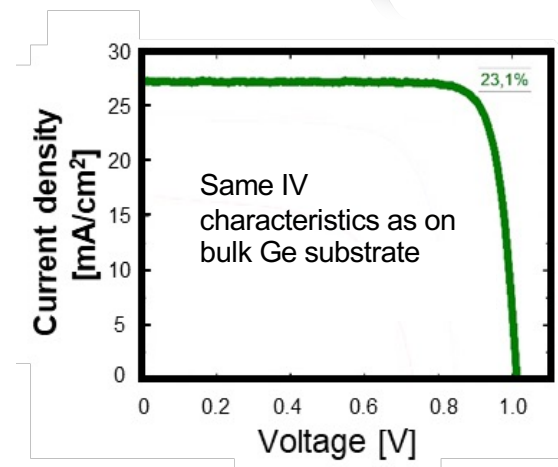
## Epi-ready porous wafers, on-target device performance



Porous 4" wafer



Porous 4" wafer after Ge epitaxy



Single-junction SC on porous 4" Ge



*Proof of  
concept:  
completed*



*Technical  
insourcing:  
2023-2025*



*Scale up:  
2025-2028*



*Full production:  
Beyond 2028*

# Recycling and Re-using Ge substrates

Lower the cost and Reduced primary material dependency

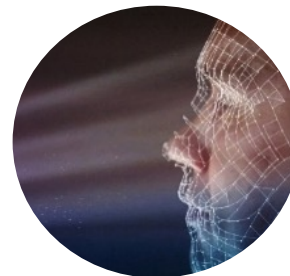
**MJ solar cells**  
Space PV



**MJ solar cells**  
CPV



**VCSELs**  
3D sensing



**SWIR sensors**  
3D sensing



**Micro-LEDs**  
VR/MR



Recycle

Wafer scraps, substrate thinning

Ge launched to orbit cannot be recycled.

Wafer scraps, substrate thinning

Substrate removal by grinding or wet etching



Reuse

Only few  $\mu\text{m}$  of Ge present in the final product, the rest is re-used.

Next generation solution for substrate removal in CMOS/backplane integration flow. Re-use instead of recycling.



# Conclusions

Ge is a high-quality epi substrate with zero EPD, allowing to manufacture new photonics devices such as long/short wavelength VCSELs, SWIR sensors and micro-LEDs.

Ge is a CMOS compatible material enabling integration between CMOS and III-V materials. Ge wafers can be removed selectively with respect to the III-V stack.

Despite geopolitical challenges in Ge sourcing, Umicore is very well positioned to supply Ge-based products to growing markets thanks to our recycling capabilities & diversified sourcing.

Umicore develops reusable Ge platform which allows to lower the costs, limit the amount of Ge in the end product and enhance CMOS integration.

**Visit our Booth – Galaxy 1 & 2, booth #2**

# Connecting Life

